December 2014

SemiHow
Know-How for Semiconductor

BV_{DSS} = 80 V

$R_{DS(on)\ typ}$ = 8.5 mΩ

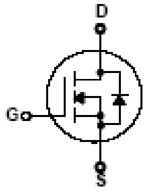
I_D = 65 A

HRP100N08K

80V N-Channel Trench MOSFET

TO-220

1.Gate 2. Drain 3. Source



FEATURES

- ☐ Originative New Design
- ☐ Superior Avalanche Rugged Technology
- ☐ Excellent Switching Characteristics
- ☐ Unrivalled Gate Charge : 73 nC (Typ.)
- ☐ Extended Safe Operating Area
- ☐ Lower $R_{DS(ON)}$: 8.5 mΩ (Typ.) @V_{GS}=10V
- ☐ 100% Avalanche Tested

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	80	V
I_D	Drain Current – Continuous (T_C = 25℃)	65	A
	Drain Current – Continuous (T_C = 100℃)	46	A
I_{DM}	Drain Current – Pulsed (Note 1)	230	A
V_{GS}	Gate-Source Voltage	±25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	210	mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	8.8	mJ
P_D	Power Dissipation (T_C = 25℃)	88	W
	- Derate above 25℃	0.59	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	℃
T_L	Maximum lead temperature for soldering purposes, 1/8” from case for 5 seconds	300	℃

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.7	℃/W
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics T_J=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 µA	2.2	--	3.8	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 40 A	--	8.5	10	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20, I_D = 40 A	--	70	--	S
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	80	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 64 V, V_{GS} = 0 V	--	--	1	µA
		V_{DS} = 64 V, T_J = 125℃	--	--	100	µA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±25 V, V_{DS} = 0 V	--	--	±100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	4900	--	pF
C_{oss}	Output Capacitance		--	300	--	pF
C_{rss}	Reverse Transfer Capacitance		--	230	--	pF
R_g	Gate Resistance	V_{GS} = 0 V, V_{DS} = 0 V, f = 1MHz	--	1.8	--	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 40 V, I_D = 30 A, R_G = 6 Ω	--	50	--	ns
t_r	Turn-On Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	130	--	ns
t_f	Turn-Off Fall Time		--	40	--	ns
Q_g	Total Gate Charge	V_{DS} = 64 V, I_D = 30 A, V_{GS} = 10 V	--	73	--	nC
Q_{gs}	Gate-Source Charge		--	20	--	nC
Q_{gd}	Gate-Drain Charge		--	20	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	65	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	230	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 30 A, V_{GS} = 0 V	--	--	1.3	V
trr	Reverse Recovery Time	I_S = 30 A, V_{GS} = 0 V di_F/dt = 100 A/µs	--	60	--	ns
Qrr	Reverse Recovery Charge		--	100	--	nC

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L=1mH, I_{AS}=17A, V_{DD}=25V, R_G=25Ω, Starting T_J =25°C

Typical Characteristics

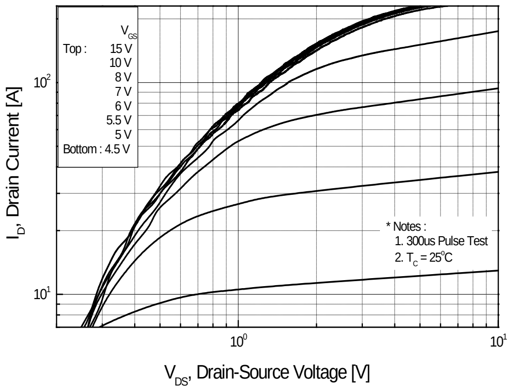


Figure 1. On Region Characteristics

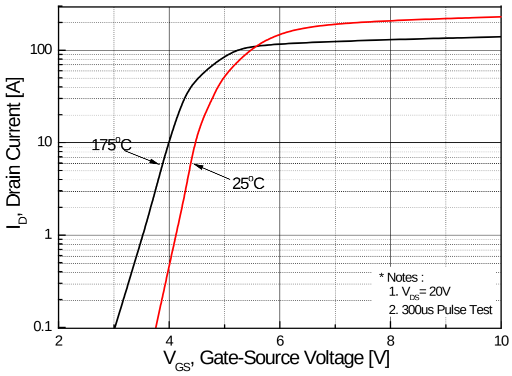


Figure 2. Transfer Characteristics

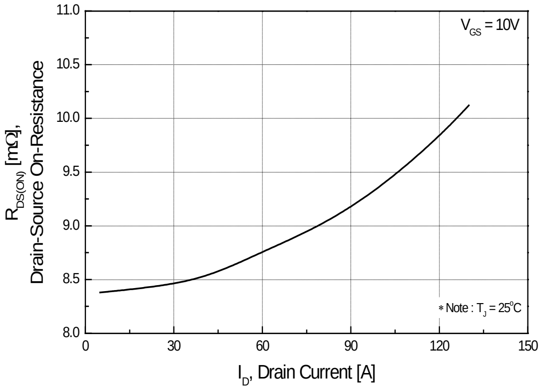


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

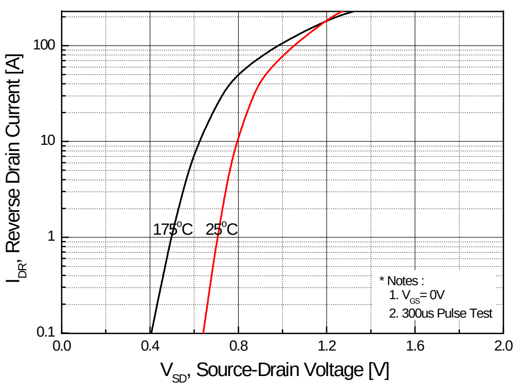


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

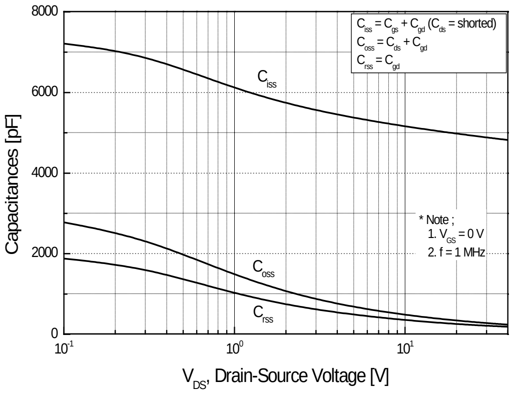


Figure 5. Capacitance Characteristics

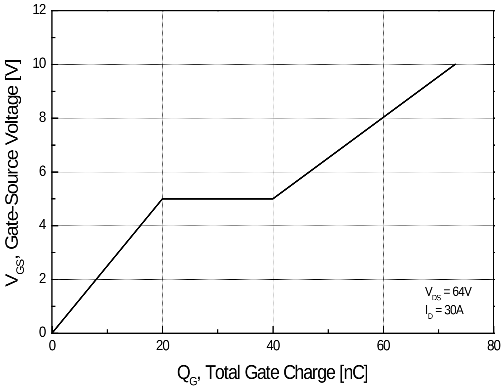


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

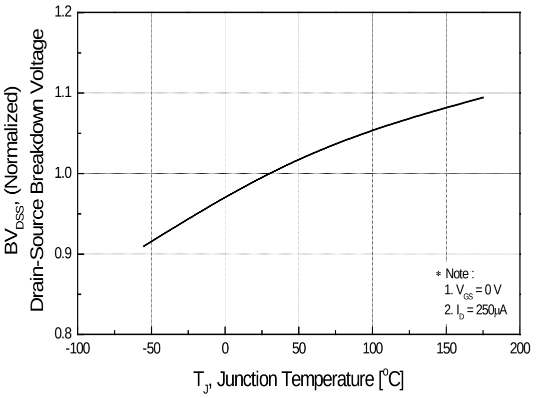


Figure 7. Breakdown Voltage Variation vs Temperature

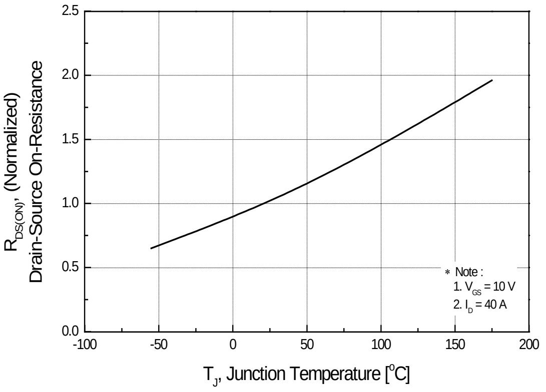


Figure 8. On-Resistance Variation vs Temperature

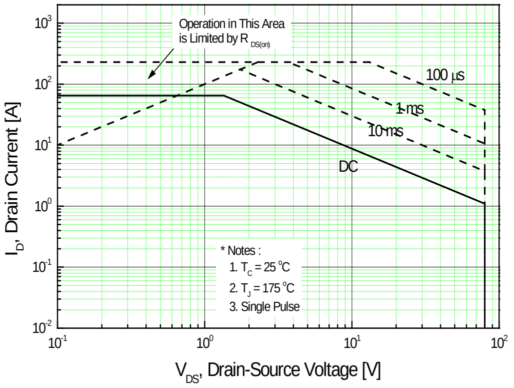


Figure 9. Maximum Safe Operating Area

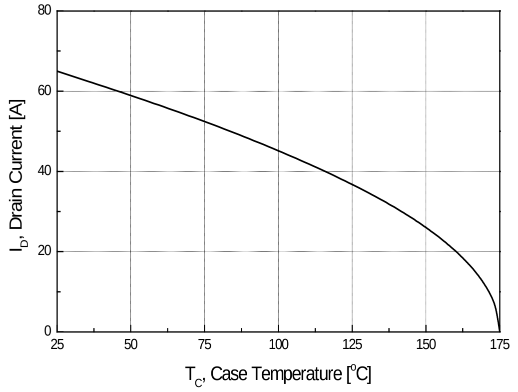


Figure 10. Maximum Drain Current vs Case Temperature

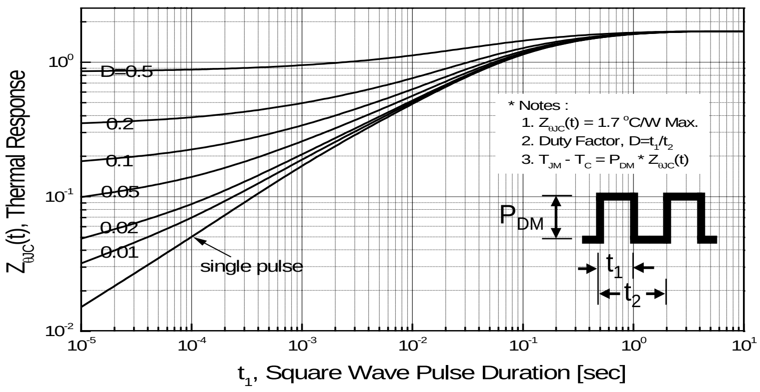


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

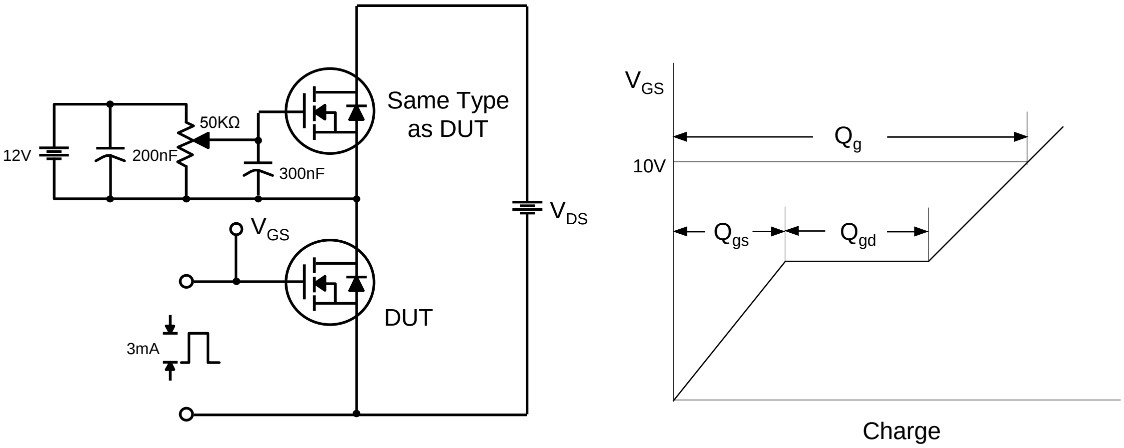


Fig 13. Resistive Switching Test Circuit & Waveforms

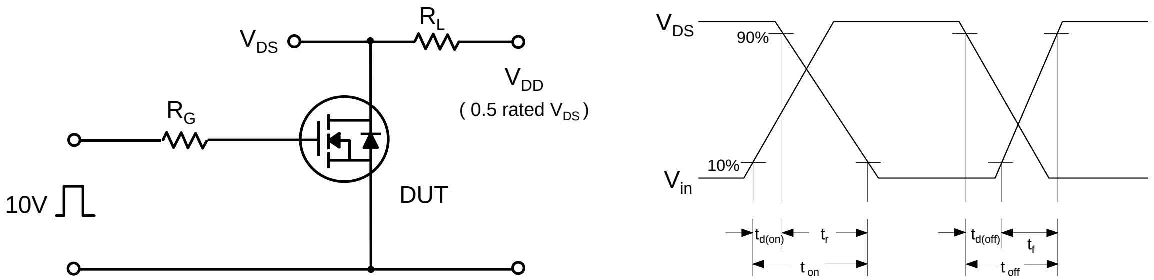
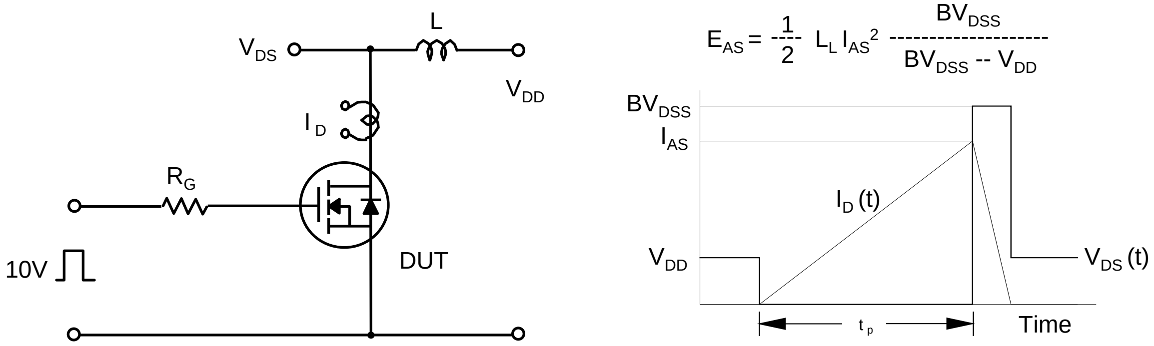
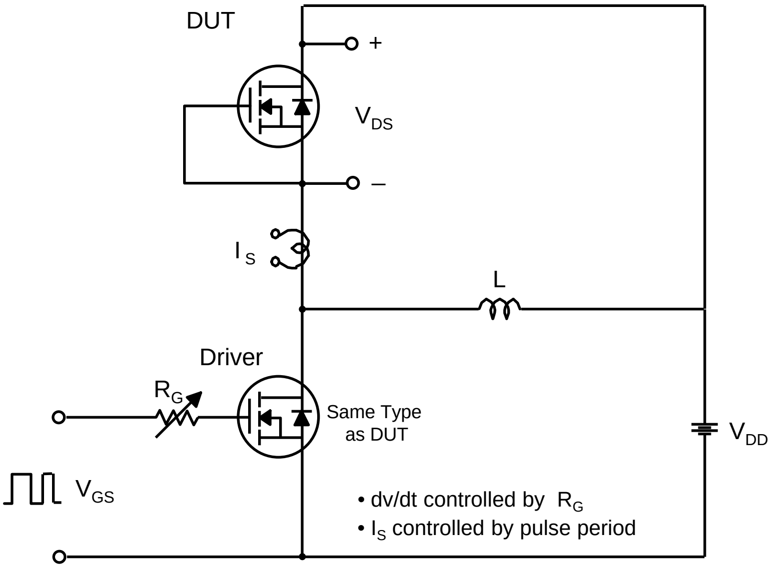


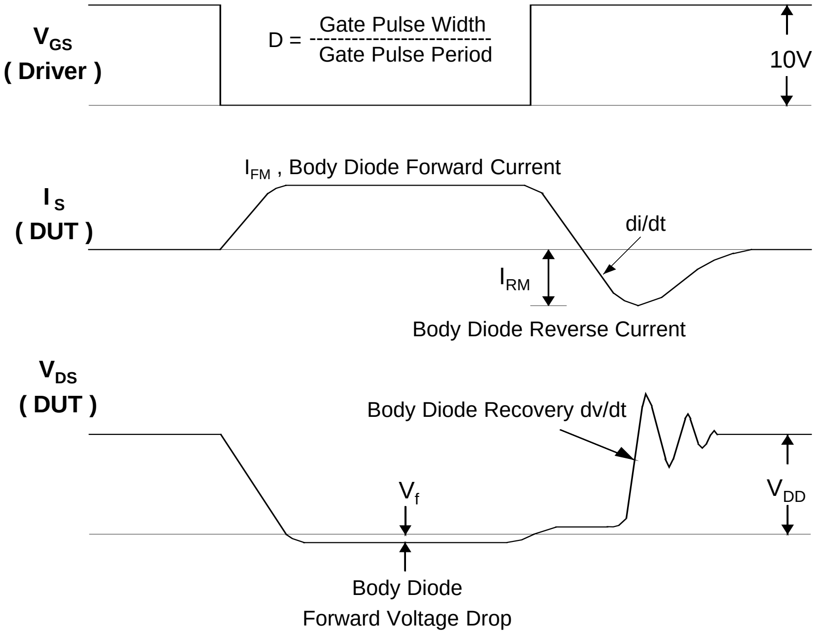
Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

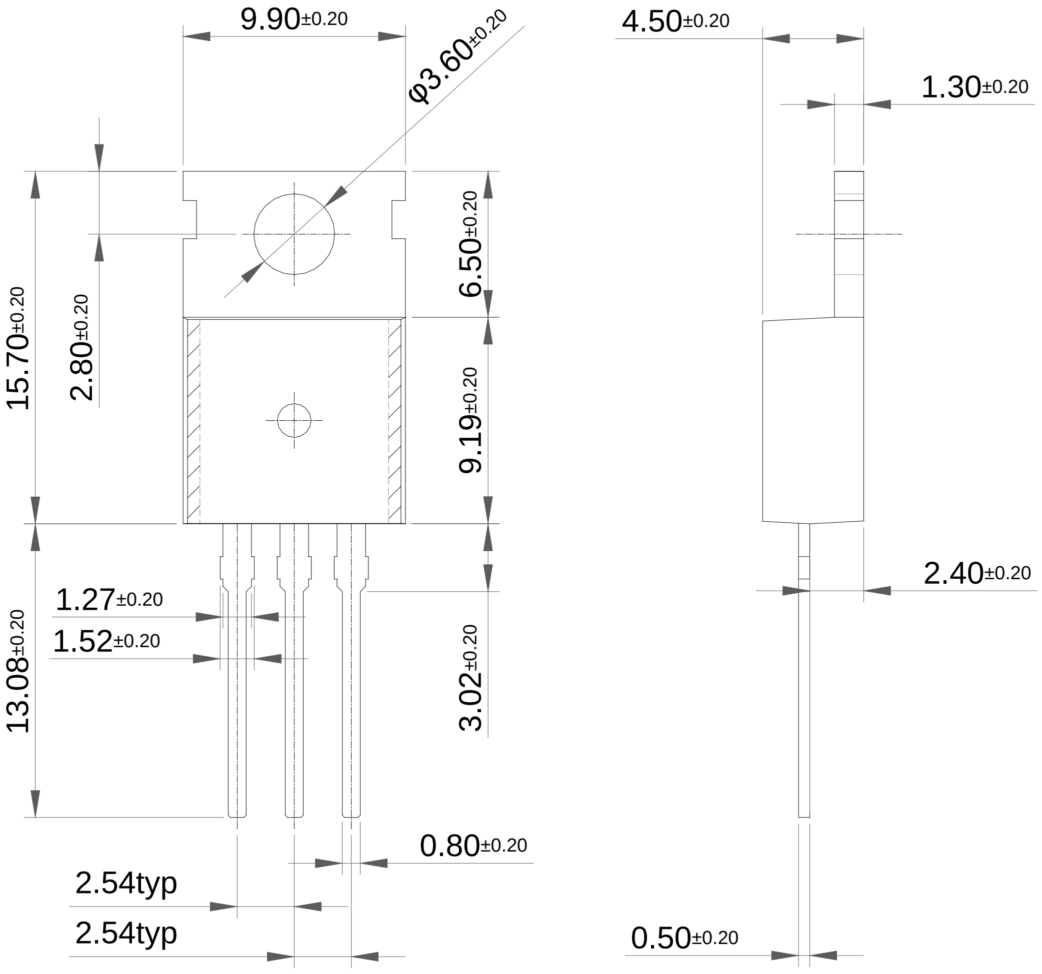
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimension

TO-220 (A)



Package Dimension

TO-220 (B)